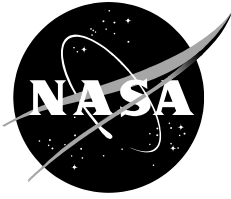


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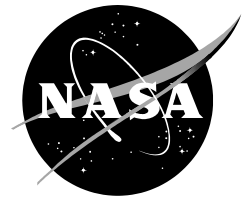
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1. Introduction

The purpose of this testing was to obtain heavy ion-induced single event upset (SEU) cross sections and error rates for the Integrated Silicon Solutions, Inc. (ISSI) IS46DR16640B-25DBA25. The test was conducted at Texas A&M University's Cyclotron Institute. Testing occurred on October 2, 2017.

2. Test Samples

The IS46DR16640B-25DBA25 is a DDR2 SDRAM from ISSI with a 64Mx16 (8Mx16x8 banks) configuration. Five (5) parts from two Lot Date Codes (LDC) for the ISSI IS46DR16640B-25DBA25 were provided for testing: 1504 and 1510. The datasheet was the March 2015 version. More information can be found in Tables 1 – 3.

Table 1: Part Identification Information

Qty	Part Number	LDC	REAG Identifier	Package
8	IS46DR16640B-25DBA25	1504	16-011	BGA-84
8	IS46DR16640B-25DBA25	1510	16-012	BGA-84

Table 2: SDRAM Address Table

Parameter	Addresses	Total
Row Addressing	A0-A12	13
Column Addressing	A0-A9	10
Bank Addressing	BA0-BA2	3
Pre-charge Addressing	A10	1

Table 3: Clock Cycle Timing

Parameter	-25D	Units
Speed Grade	DDR2-800D	
CL-tRCD-tRP	5-5-5	tCK
tCK(CL=3)	5	ns
tCK(CL=4)	3.75	ns
tCK(CL=5)	2.5	ns
tCK(CL=6)	2.5	ns
tCK(CL=7)	2.5	ns
Frequency (max)	400	MHz

3. Test Facility

Facility:	Texas A&M University Cyclotron Institute
Ions (Energies MeV/amu):	Ne, Kr, Xe, Ar
Angles	0°, 30°, 60°
LETs (MeV-cm²/mg):	1.9 – 55.5
In Vacuum (y/n):	No

4. Test Conditions and Error Modes

Test Temperature:	Room temperature
Power Supply Voltages:	1.8 V _{DC}
Run Type	Static, Dynamic, Random
Error Modes:	SEUs, SEFIs, Bursts of errors independent of SEFIs

5. Test Methods

Equipment necessary:

A project-developed test setup by Jackson & Tull (J&T) contractors was used for testing. The DDR2 die was mounted on SODIMMs and then tested using a Xilinx ML507 evaluation board with the external power supply connector attached to an Agilent N6702B for external power. The 1.8V power supply for the DUT was isolated by disabling the regulator on the evaluation board and connecting a laboratory DC supply; both were controlled via LabView. The DDR2 die was thinned to 100 μm for testing. Figure 1 shows an image of the evaluation board used.

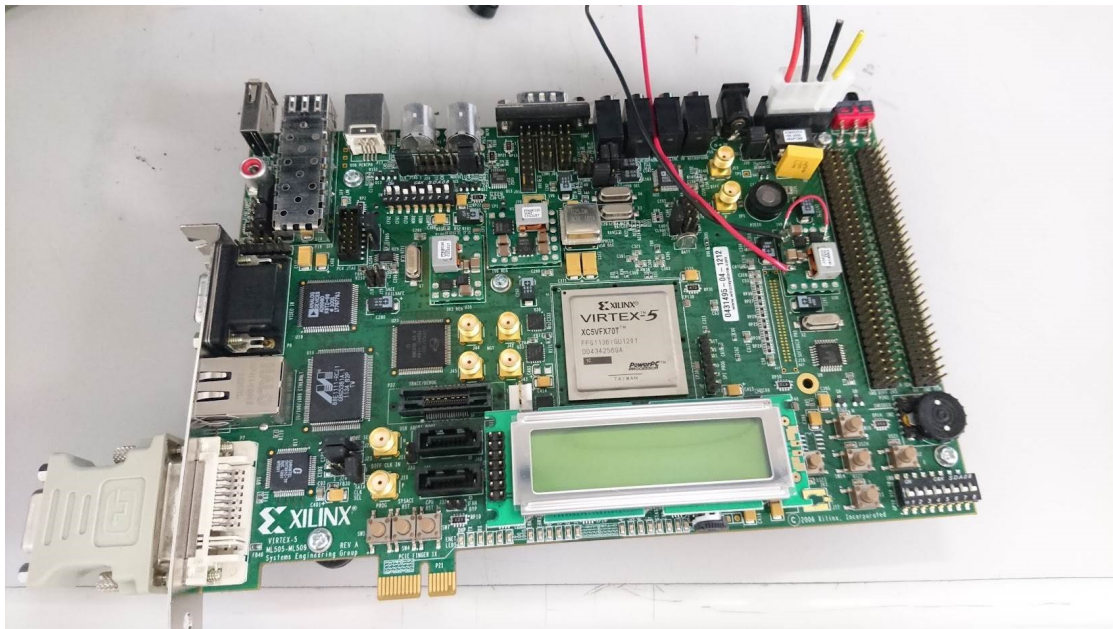


Figure 1. Evaluation board used for SEE testing of DDR2.

Test Performance

The test was performed by Ted Wilcox (GSFC-561), Michael Campola (GSFC-561), Madhu Kadari (J&T), and Seshagiri Nadendla (J&T).

Test Sequence:

Testing was done using a broadbeam ion beam whose diameter is larger than the device, so every part of the device was equally likely to be struck by an ion. Testing was done on five (5) devices, all biased at a nominal operating voltage of 1.8 V. Table 5, on the following 3 pages, lays out the test sequence; the full run log can be found in Section 7 – Run Log.

Table 5: Test Execution Sequence

Run #	Device	Thickness (μm)	LDC	RunType	Memory Space (bits)	Ion	MeV/amu	Eff, LET (MeV-cm ² /mg)	Angle (°)	Avg Flux (s ⁻¹ cm ⁻²)	Fluence (cm ⁻²)	Live Time (s)
1	1	133	1510	static	1073741824	Ne	21.5	1.9	0	1.00E+04	5.00E+05	51.4
2	1	133	1510	static	1073741824	Ne	21.5	1.9	0	1.00E+04	1.00E+06	130.5
3	1	133	1510	static	1073741824	Ne	18.7	4.3	60	1.00E+04	1.00E+06	192.1
4	1	133	1510	dynamic	33554432	Ne	18.7	4.3	60	1.00E+04	1.00E+06	216.9
5	1	133	1510	dynamic	33554432	Ne	18.7	4.3	60	1.00E+04	1.00E+06	-
6	1	133	1510	static	1073741824	Kr	14.5	25.8	0	1.00E+04	1.00E+06	92.3
7	1	133	1510	static	1073741824	Kr	14.5	25.8	0	1.00E+04	1.00E+06	71
8	1	133	1510	dynamic	33554432	Kr	14.5	25.8	0	1.00E+04	1.00E+06	72.6
9	1	133	1510	random	1073741824	Kr	14.5	25.8	0	1.00E+04	1.00E+06	71
10	8	138	1504	static	1073741824	Kr	14.5	25.8	0	1.60E+04	1.00E+06	67
11	8	138	1504	static	1073741824	Kr	14.5	25.8	0	1.60E+04	1.00E+06	54
12	8	138	1504	dynamic	33554432	Kr	14.5	25.8	0	1.60E+04	1.00E+06	62
13	8	138	1504	dynamic	33554432	Kr	14.5	25.8	0	1.60E+04	1.00E+06	54
14	8	138	1504	random	1073741824	Kr	14.5	25.8	0	1.00E+04	1.00E+06	95
15	8	138	1504	static	1073741824	Kr	14.5	31.4	30	1.00E+04	8.50E+05	102
16	8	138	1504	static	1073741824	Kr	14.5	31.4	30	1.00E+04	1.00E+06	102
17	8	138	1504	dynamic	33554432	Kr	14.5	31.4	30	1.00E+04	1.00E+06	82
18	8	138	1504	dynamic	33554432	Kr	14.5	31.4	30	1.40E+04	1.00E+06	80
19	8	138	1504	dynamic	33554432	Kr	14.5	31.4	30	1.40E+04	1.00E+06	82
20	8	138	1504	random	1073741824	Kr	14.5	31.4	30	1.50E+04	1.00E+06	82
21	9	87	1504	static	1073741824	Kr	16.7	27.8	30	1.00E+04	1.00E+06	113
22	9	87	1504	static	1073741824	Kr	16.7	23.4	0	0.00E+00	0.00E+00	0
23	9	87	1504	static	1073741824	Kr	16.7	23.4	0	1.00E+04	4.46E+04	0
24	9	87	1504	static	1073741824	Kr	16.7	23.4	0	1.00E+04	1.00E+06	81
25	9	87	1504	static	1073741824	Xe	15.5	46.7	0	5.00E+03	1.00E+05	18

Run #	Device	Thickness (μm)	LDC	RunType	Memory Space (bits)	Ion	MeV/amu	Eff, LET (MeV-cm ² /mg)	Angle (°)	Avg Flux (s ⁻¹ cm ⁻²)	Fluence (cm ⁻²)	Live Time (s)
26	9	87	1504	static	1073741824	Xe	15.5	46.7	0	5.00E+03	1.00E+05	25
27	9	87	1504	dynamic	33554432	Xe	15.5	46.7	0	5.00E+03	1.00E+05	28
28	9	87	1504	dynamic	33554432	Xe	15.5	46.7	0	5.00E+03	5.00E+05	124
29	9	87	1504	random	1073741824	Xe	15.5	46.7	0	3.00E+04	1.00E+07	350
30	9	87	1504	static	1073741824	Xe	15.5	55.5	30	3.00E+04	1.00E+06	40
31	9	87	1504	static	1073741824	Xe	15.5	55.5	30	3.00E+04	5.00E+05	56
32	9	87	1504	dynamic	33554432	Xe	14.4	55.5	30	1.00E+04	5.00E+05	50
33	9	87	1504	dynamic	33554432	Xe	14.4	55.5	30	1.00E+04	5.00E+05	50
34	9	87	1504	random	1073741824	Xe	15.5	55.5	30	3.00E+04	1.00E+07	480
35	9	87	1504	random edit	1073741824	Xe	15.5	55.5	30	2.00E+04	7.00E+06	394
36	9	87	1504	random edit	1073741824	Xe	15.5	46.7	0	2.00E+04	1.12E+06	36
37	9	87	1504	random edit	1073741824	Xe	15.5	46.7	0	2.00E+04	2.81E+06	107
38	9	87	1504	random edit	1073741824	Xe	15.5	46.7	0	2.00E+04	1.24E+06	46
39	9	87	1504	random edit	1073741824	Xe	15.5	55.5	30	2.00E+04	4.41E+05	25
40	9	87	1504	random edit	1073741824	Ar	20.2	7.3	30	1.00E+04	5.00E+06	493
41	9	87	1504	random edit	1073741824	Ar	20.2	7.3	30	5.00E+04	5.00E+06	118
42	2	132	1510	static	1073741824	Ar	18.1	7.8	30	5.00E+04	1.00E+06	22
43	2	132	1510	static	1073741824	Ar	18.1	7.8	30	5.00E+04	5.00E+06	120
44	2	132	1510	dynamic	33554432	Ar	18.1	7.8	30	5.00E+04	5.00E+06	120
45	2	132	1510	dynamic	33554432	Ar	18.1	7.8	30	5.00E+04	5.00E+06	130
46	2	132	1510	random edit	1073741824	Ar	18.1	7.8	30	5.00E+04	5.00E+06	130
47	2	132	1510	random edit	1073741824	Ar	13.2	16.7	60	5.00E+04	6.14E+05	26
48	2	132	1510	random edit	1073741824	Ar	13.2	16.7	60	5.00E+04	5.00E+06	195
49	2	132	1510	static	1073741824	Ar	13.2	16.7	60	5.00E+04	5.00E+06	195
50	2	132	1510	static	1073741824	Ar	13.2	16.7	60	1.00E+04	1.00E+05	20
51	2	132	1510	static	1073741824	Ar	13.2	16.7	60	1.00E+04	5.00E+05	97

Run #	Device	Thickness (μm)	LDC	RunType	Memory Space (bits)	Ion	MeV/amu	Eff, LET (MeV-cm ² /mg)	Angle (°)	Avg Flux (s ⁻¹ cm ⁻²)	Fluence (cm ⁻²)	Live Time (s)
52	2	132	1510	static	1073741824	Ar	18.9	6.6	0	1.00E+04	5.00E+05	53
53	2	132	1510	random edit	1073741824	Ar	18.9	6.6	0	1.00E+04	1.00E+06	130
54	2	132	1510	random edit	1073741824	Ar	18.9	6.6	0	1.00E+04	7.26E+04	7
55	2	132	1510	random edit	1073741824	Ar	18.9	6.6	0	1.00E+04	4.00E+06	347
56	2	132	1510	random edit	1073741824	Ar	13.2	16.7	0	1.00E+04	5.00E+06	825
57	3	99	1510	random edit	1073741824	Ar	16.3	14.6	60	1.30E+04	4.41E+06	703
58	3	99	1510	static	1073741824	Ar	16.3	14.6	60	1.30E+04	1.00E+06	184
59	3	99	1510	static	1073741824	Ar	20.2	6.3	0	1.30E+04	2.00E+06	132
60	3	99	1510	random edit	1073741824	Ar	20.2	6.3	0	1.30E+04	4.23E+06	278
61	3	99	1510	random edit	1073741824	Ar	20.2	6.3	0	1.30E+04	1.33E+06	91
62	3	99	1510	random edit	1073741824	Ar	20.2	6.3	0	1.30E+04	4.61E+06	307
63	3	99	1510	random edit	1073741824	Ne	22.2	1.9	0	3.00E+04	4.65E+06	137

6. Results

Three sets of cross-section conditions were obtained from testing: SEUs during static operation, SEUs during dynamic operation, and SEFI/Burst events. Figures 2 – 4 show the cross-section curves for the different categories, along with the associated Weibull curves; the Weibull parameters are provided in Table 6.

Table 6: Weibull Parameters

SEU Condition	LET _{th} (MeV·cm ² /mg)	Width (MeV·cm ² /mg)	Exponent	Limiting Cross-Section (cm ²)
Static	2.0	80.00	3.500	5.00e-11
Dynamic	2.0	150.0	3.000	1.00E-09
SEFI/Burst	4.3	170.8	0.582	3.00E-06

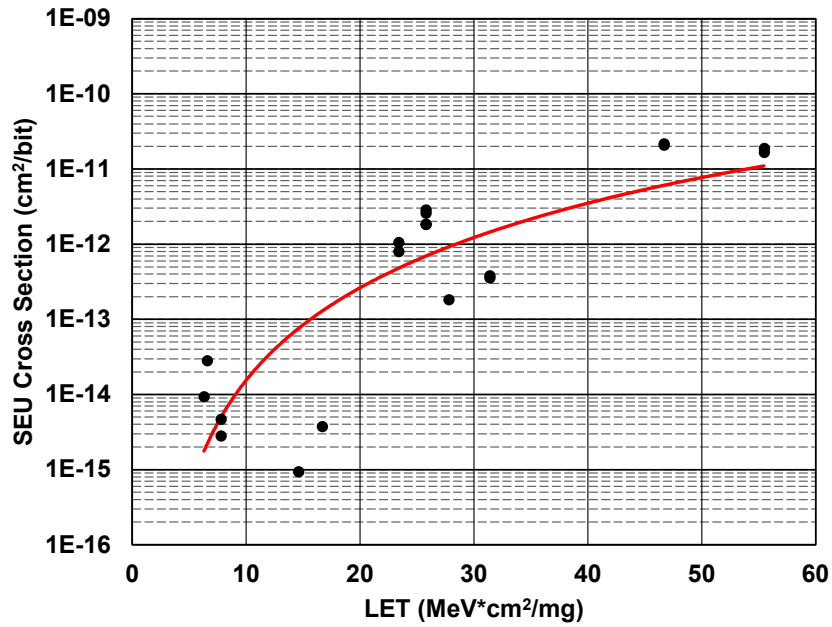


Figure 2. Cross-section vs LET for SEUs during static operation. Weibull fit shown in red.

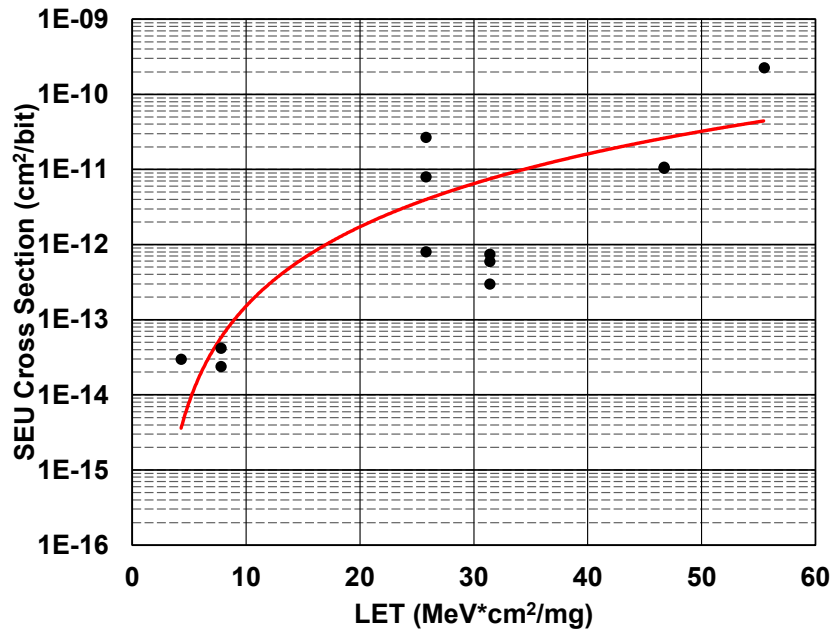


Figure 3. Cross-section vs LET for SEUs during dynamic operation. Weibull fit shown in red.

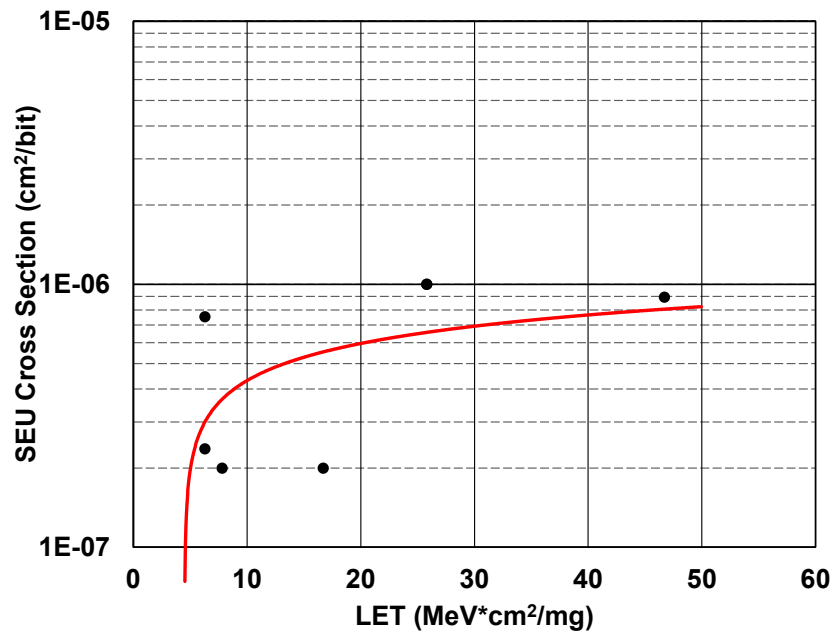


Figure 4. Cross-section vs LET for SEFIs and Burst events. Weibull fit shown in red. SEFI cross-section dominates the response.

